



FUKUCOM COMPANY LTD.

福 灵 有 限 公 司

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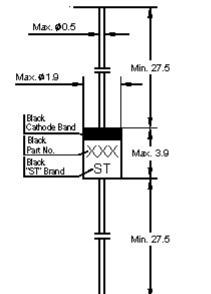
BAT85

SCHOTTKY BARRIER DIODE

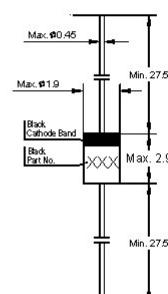
Ultra high-speed switching, switching, voltage clamping
protection circuits and blocking applications

Features

- Low forward voltage
- Hermetically-sealed leadless glass package



Glass Case DO-35
Dimensions in mm



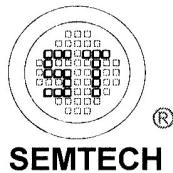
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	30	V
Continuous Forward Current	I_F	200	mA
Average Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	I_{FRM}	300	mA
Non-Repetitive Peak Forward Current	I_{FSM}	5	A
Thermal Resistance from Junction to Ambient	R_{thja}	320	K/W
Operating Ambient Temperature	T_{amb}	- 65 to + 125	$^\circ\text{C}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_S	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1 \text{ mA}$	V_F	240	mV
at $I_F = 1 \text{ mA}$	V_F	320	mV
at $I_F = 10 \text{ mA}$	V_F	400	mV
at $I_F = 30 \text{ mA}$	V_F	500	mV
at $I_F = 100 \text{ mA}$	V_F	800	mV
Reverse Current at $V_R = 25 \text{ V}$	I_R	2	μA
Diode Capacitance at $V_R = 1 \text{ V}, f = 1 \text{ MHz}$	C_d	10	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}, I_R = 10 \text{ mA}, R_L = 100 \Omega$	t_{rr}	4	ns



SEMTECH

Dated : 20/06/2007